

**Electrical Characteristics** at  $T_A$  = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics		•	•		•
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	4.5	5	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-emitter cutoff current	I <sub>CES</sub>	-	-	10	μA
$V_{CE} = 15 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I <sub>CBO</sub>	-	_	100	nA
$V_{\rm CB} = 5 \text{ V}, I_{\rm E} = 0$					
Emitter-base cutoff current	I <sub>EBO</sub>	-	_	3	μA
$V_{\rm EB} = 0.5  \text{V}, I_{\rm C} = 0$					
DC current gain	h <sub>FE</sub>	60	95	130	-
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 4 V, pulse measured					

 $<sup>^{1}</sup>$ For the definition of  $R_{\mathrm{thJS}}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

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**Electrical Characteristics** at  $T_A$  = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random samplin	g)				,
Transition frequency	$f_{T}$	18	25	-	GHz
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 3 V, $f$ = 2 GHz					
Collector-base capacitance	C <sub>cb</sub>	-	0.15	0.3	pF
$V_{\text{CB}} = 2 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$ ,					
emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	-	0.37	-	
$V_{CE} = 2 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,					
base grounded					
Emitter-base capacitance	C <sub>eb</sub>	-	0.55	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$ ,					
collector grounded					
Minimum noise figure	NF <sub>min</sub>	-	1.1	-	dB
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 2 V, $f$ = 1.8 GHz, $Z_{\rm S}$ = $Z_{\rm Sopt}$					
Power gain, maximum stable <sup>1)</sup>	G <sub>ms</sub>	-	21	-	dB
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
$Z_{L} = Z_{Lopt}$ , $f = 1.8 \text{ GHz}$					
Insertion power gain	$ S_{21} ^2$	14	17	-	
$V_{CE} = 2 \text{ V}, I_{C} = 20 \text{ mA}, f = 1.8 \text{ GHz},$					
$Z_{\rm S} = Z_{\rm L} = 50 \ \Omega$					
Third order intercept point at output <sup>2)</sup>	IP3	-	22	-	dBm
$V_{CE} = 2 \text{ V}, I_{C} = 20 \text{ mA}, f = 1.8 \text{ GHz},$					
$Z_{\rm S} = Z_{\rm L} = 50 \ \Omega$					
1dB compression point at output	P <sub>-1dB</sub>	-	12	-	
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 2 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
f = 1.8 GHz					

 $<sup>^{1}</sup>G_{ms} = |S_{21} / S_{12}|$ 

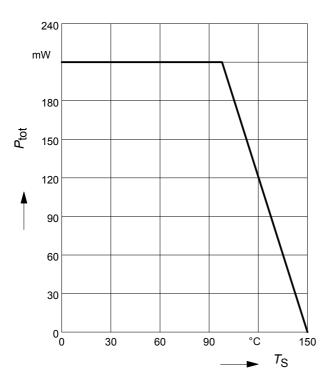
<sup>&</sup>lt;sup>2</sup>IP3 value depends on termination of all intermodulation frequency components.

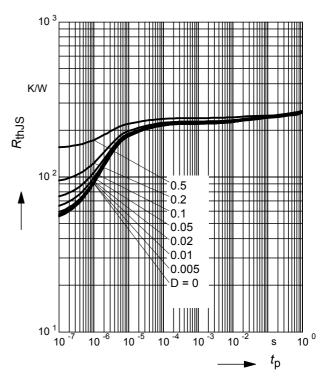
Termination used for this measurement is  $50\Omega$  from 0.1 MHz to 6 GHz



# Total power dissipation $P_{tot} = f(T_S)$

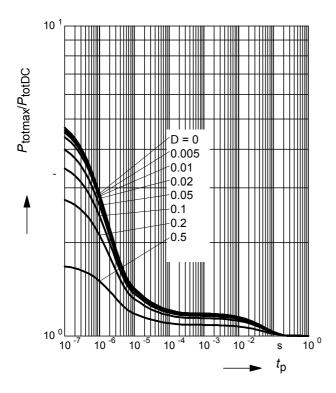
## Permissible Pulse Load $R_{thJS} = f(t_p)$



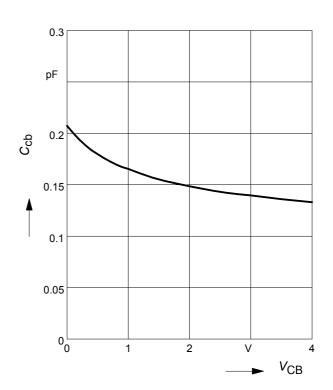


### **Permissible Pulse Load**

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$ 



**Collector-base capacitance**  $C_{cb}$ =  $f(V_{CB})$  f = 1MHz

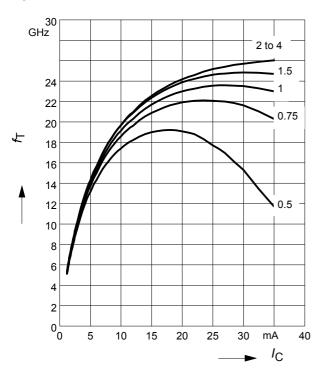




### Transition frequency $f_T = f(I_C)$

f = 2 GHz

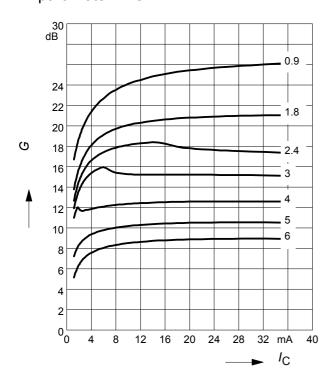
 $V_{CE}$  = parameter in V



Power gain  $G_{ma}$ ,  $G_{ms} = f(I_C)$ 

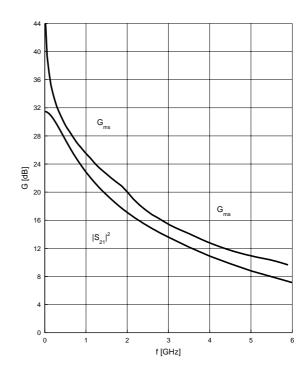
 $V_{CE} = 2V$ 

f = parameter in GHz



# **Power gain** $G_{ma}$ , $G_{ms}$ , $|S_{21}|^2 = f(f)$

 $V_{CE} = 2 \text{ V}, I_{C} = 20 \text{ mA}$ 

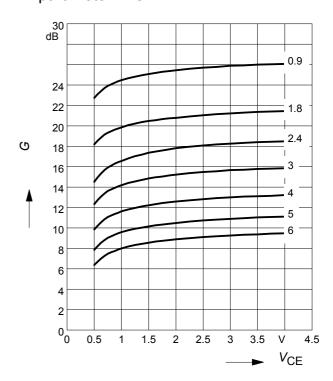


# Power gain $G_{ma}$ , $G_{ms} = f(V_{CE})$

 $I_{\rm C}$  = 20 mA

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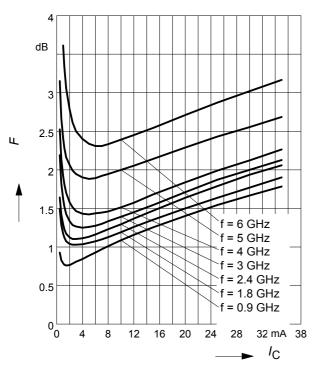
f = parameter in GHz





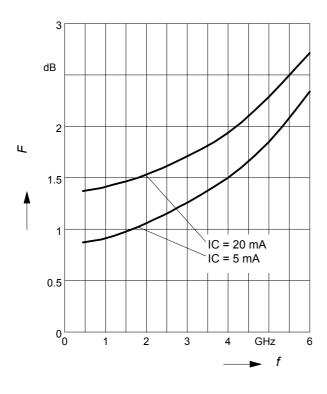
Noise figure  $F = f(I_C)$ 

$$V_{CE}$$
 = 2 V,  $Z_{S}$  =  $Z_{Sopt}$ 



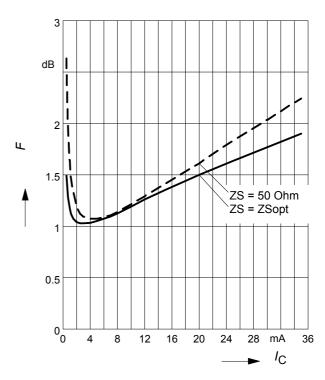
Noise figure F = f(f)

$$V_{CE}$$
 = 2 V,  $Z_{S}$  =  $Z_{Sopt}$ 



Noise figure  $F = f(I_C)$ 

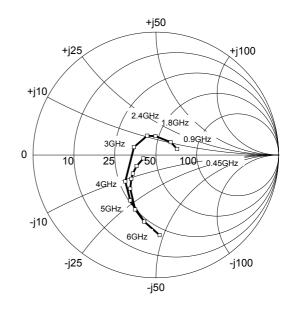
$$V_{CE} = 2 \text{ V}, f = 1.8 \text{ GHz}$$



Source impedance for min.

noise figure vs. frequency

$$V_{\rm CE}$$
 = 2 V,  $I_{\rm C}$  = 5 mA / 20 mA





#### SPICE GP Model

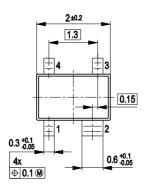
For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website www.infineon.com/rf.models.

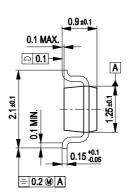
Please consult our website and download the latest versions before actually starting your design. You find the BFP420 SPICE GP model in the internet in MWO- and ADS-format, which you can import into these circuit simulation tools very quickly and conveniently. The model already contains the package parasitics and is ready to use for DC and high frequency simulations. The terminals of the model circuit correspond to the pin configuration of the device. The model parameters have been extracted and verified up to 10 GHz using typical devices. The BFP420 SPICE GP model reflects the typical DC- and RF-performance within the limitations which are given by the SPICE GP model itself. Besides the DC characteristics all S-parameters in magnitude and phase, as well as noise figure (including optimum source impedance, equivalent noise resistance and flicker noise) and intermodulation have been extracted.



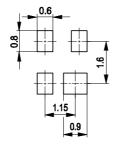
## Package Outline



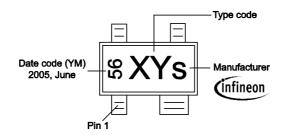




### **Foot Print**

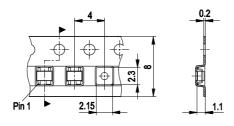


## Marking Layout (Example)



### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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